Abstracts

10-GHz 10-W Internally Matched Flip-Chip GaAs Power FET’s (Apr. 1981 [T-MTT])

Y. Mitsui, M. Kobiki, M. Wataze, K. Segawa, M. Otsubu and T. Ishii. "10-GHz 10-W Internally Matched Flip-Chip GaAs Power FET’s (Apr. 1981 [T-MTT])." 1981 Transactions on Microwave Theory and Techniques 29.4 (Apr. 1981 [T-MTT]): 304-309.

A newly developed internally matched configuration for a flip-chip GaAs power field effect transistor is presented. In this structure, gate and drain electrodes of the FET chips are directly connected to the lumped dielectric capacitors in the matching networks by thermocompression bonding using no wire. A power output of 10 W with 3-dB gain and a power added efficiency as high as 14 percent has been realized at 10 GHz.

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